

Notice of References Cited	Application/Control No. 10/593,809	Applicant(s)/Patent Under Reexamination NARAYAN ET AL.	
	Examiner JONATHAN C. LANGMAN	Art Unit 1794	Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-			
	B	US-			
	C	US-			
	D	US-			
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	O					
	P					
	Q					
	R					
	S					
	T					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Zhang et al. ("Formation of Low Resistivity Alpha Ta by Ion Sputtering"), Journal of Vacuum Science and Technology B, Vol. 21, Issue 1, Jan/Feb 2003, pgs. 237-240.
	V	Yuan et al. ("A New Method for Deposition of Cubic Ta Diffusion Barrier for Cu Metallization"), Thin Solid Films, Vol. 434, May 2003, pgs 126-129.
	W	Chen et al. ("Phase Formation behavior and Diffusion Barrier Property of Reactively Sputtered Tantalum Based Thin Films used in Semiconductor Metallization"), Thin Solid Films, Vol. 353, 1999, pgs. 264-273.
	X	

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.